

ABSTRACT OF THE DISCLOSURE

An apparatus for supplying a process gas onto a wafer includes a plurality of nozzles integrated with an electrode plate of an upper electrode. The nozzles are configured so that the flow rate of the process gas towards the wafer is greater at locations across from the outer peripheral portion of the wafer than from a location across from the center of the wafer. The plurality of nozzles thus can distribute the gas so that the density of the gas is uniform across the entire upper surface of the wafer.